

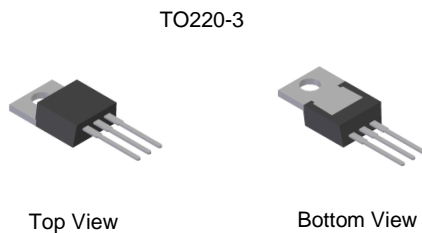
## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> T <sub>C</sub> = +25°C (Note 9)
60V	3.65mΩ @ V <sub>GS</sub> = 10V	100A

## Description and Applications

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

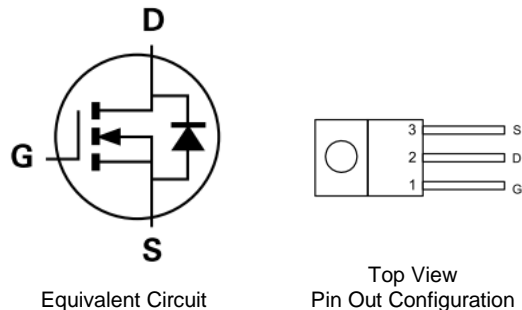


## Features

- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low Input Capacitance
- Low Input/Output Leakage
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: TO220-3
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ③
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)

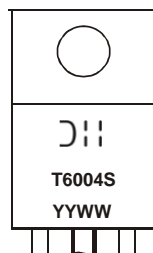


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6004SCT	TO220-3	50 pieces/tube

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, “Green” and Lead-free.
  3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



- DII = Manufacturer’s Marking
- T6004S = Product Type Marking Code
- YYWW = Date Code Marking
- YY or YY = Last Two Digits of Year (ex: 15 = 2015)
- WW or WW = Week Code (01 to 53)

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	60	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 6)	$I_D$	$T_C = +25^\circ\text{C}$ (Note 9)	100
		$T_C = +70^\circ\text{C}$	100
Maximum Continuous Body Diode Forward Current (Note 6)	$I_S$	100	A
Pulsed Drain Current (10 $\mu\text{s}$ pulse, duty cycle = 1%)	$I_{DM}$	180	A
Avalanche Current, $L=0.2\text{mH}$	$I_{AS}$	45	A
Avalanche Energy, $L=0.2\text{mH}$	$E_{AS}$	200	mJ

**Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	$P_D$	2.3	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	52.8	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)	$P_D$	113	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	1.1	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 1\text{mA}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 48\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	3.1	3.65	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 100\text{A}$
Diode Forward Voltage	$V_{SD}$	—	—	1.3	V	$V_{GS} = 0\text{V}, I_S = 100\text{A}$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	—	4556	—	pF	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	$C_{oss}$	—	1383	—		
Reverse Transfer Capacitance	$C_{rss}$	—	105	—		
Gate Resistance	$R_G$	—	0.7	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge	$Q_g$	—	95.4	—	nC	$V_{DD} = 30\text{V}, I_D = 90\text{A}, V_{GS} = 10\text{V}$
Gate-Source Charge	$Q_{gs}$	—	21.6	—		
Gate-Drain Charge	$Q_{gd}$	—	20.4	—		
Turn-On Delay Time	$t_{D(ON)}$	—	14.3	—	ns	$V_{DD} = 30\text{V}, V_{GS} = 10\text{V}, I_D = 90\text{A}, R_G = 3.5\Omega$
Turn-On Rise Time	$t_R$	—	99.1	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	40	—		
Turn-Off Fall Time	$t_F$	—	17.6	—		
Reverse Recovery Time	$t_{RR}$	—	50.5	—	ns	$I_F = 48\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	$Q_{RR}$	—	80.8	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on infinite heat sink.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.
  - Package limited.

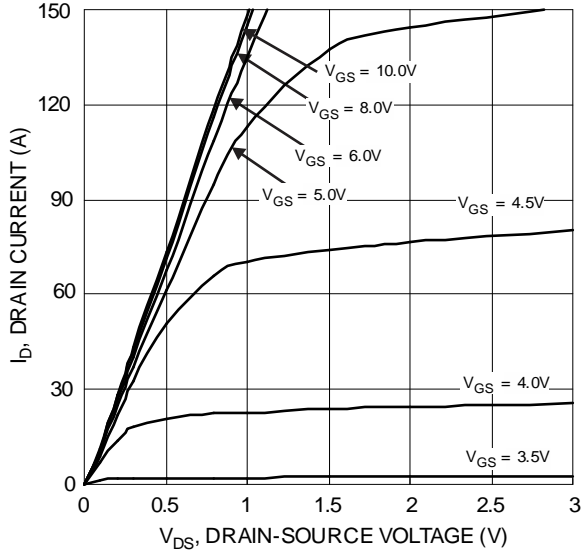


Figure 1 Typical Output Characteristic

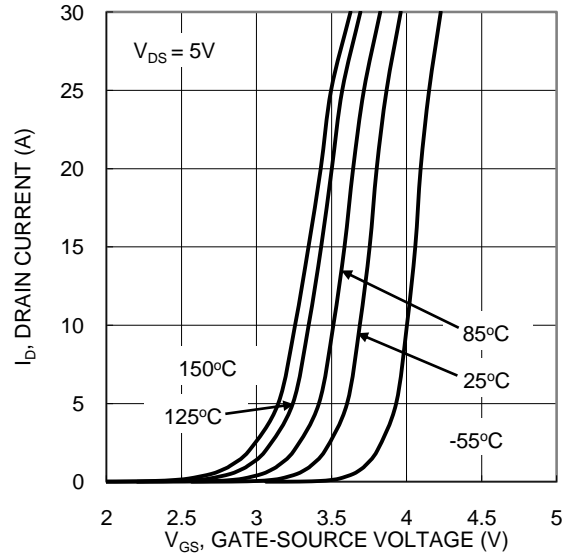


Figure 2 Typical Transfer Characteristic

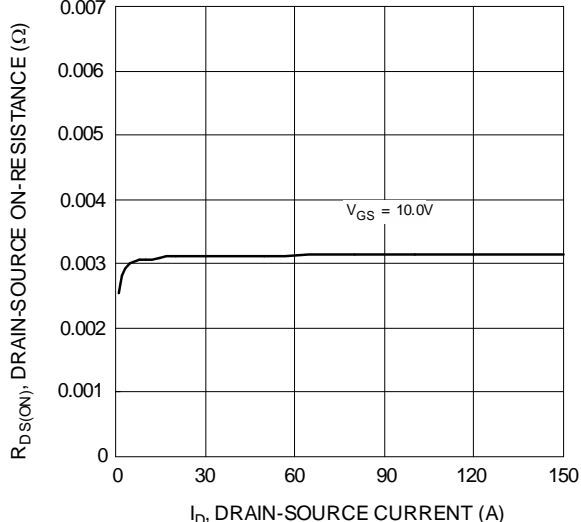


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

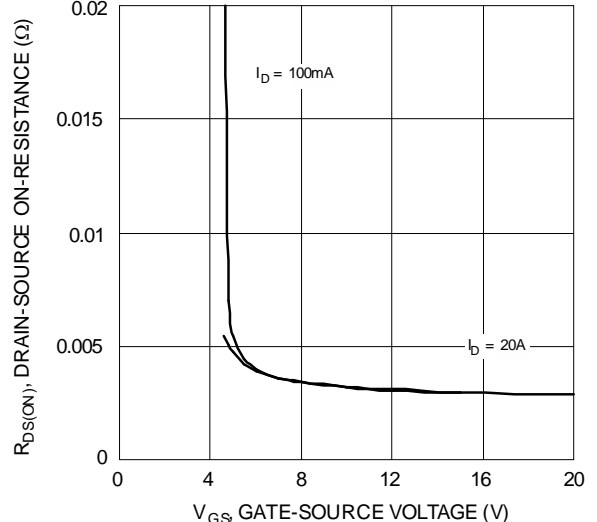


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

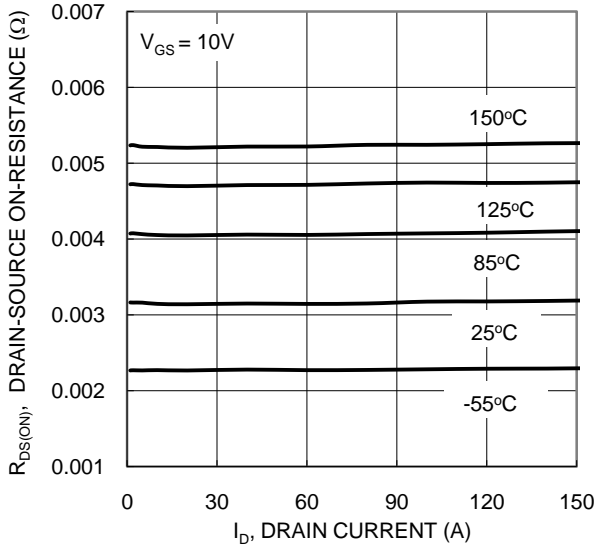


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

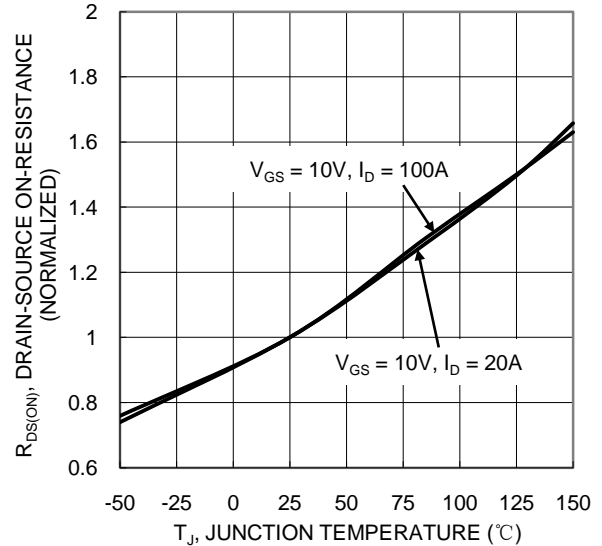


Figure 6 On-Resistance Variation with Temperature

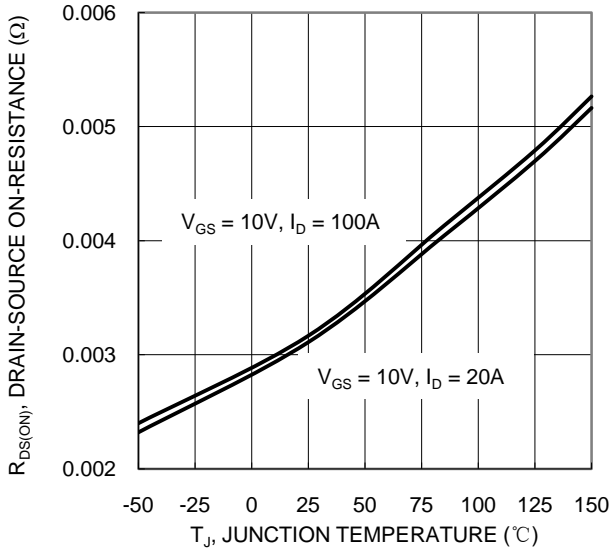


Figure 7 On-Resistance Variation with Temperature

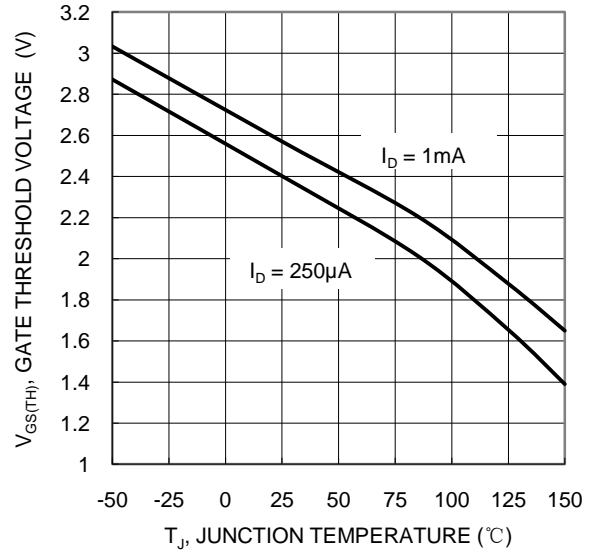


Figure 8 Gate Threshold Variation vs. Temperature

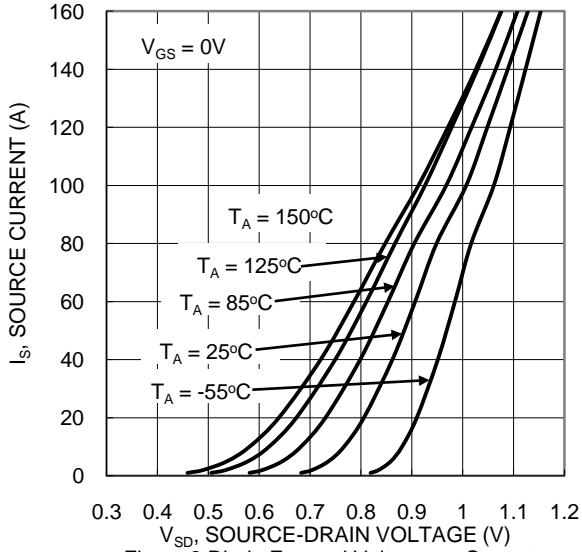


Figure 9 Diode Forward Voltage vs. Current

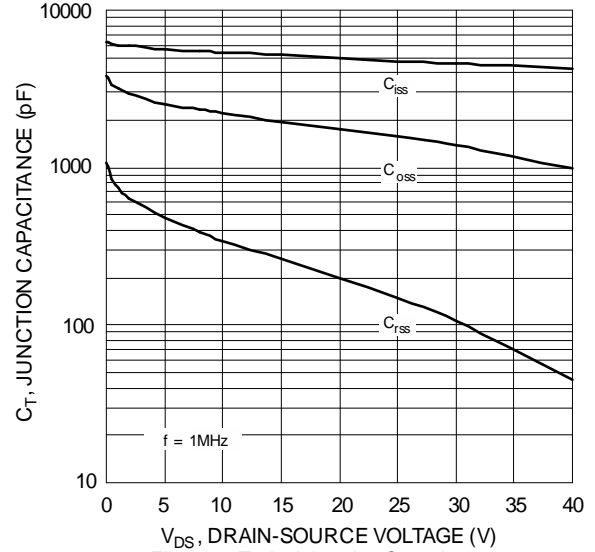


Figure 10 Typical Junction Capacitance

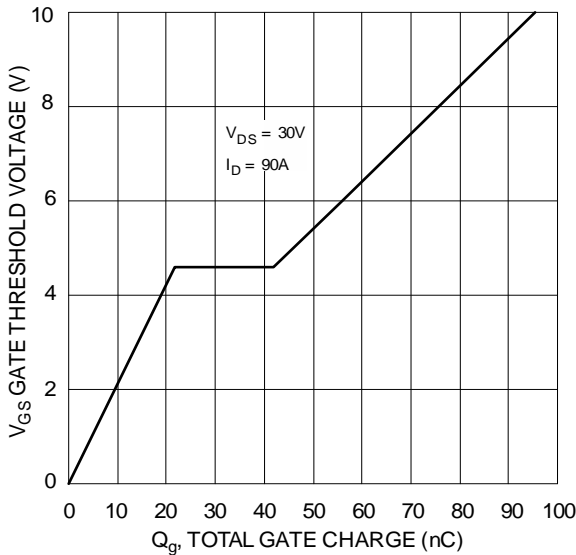


Figure 11 Gate Charge

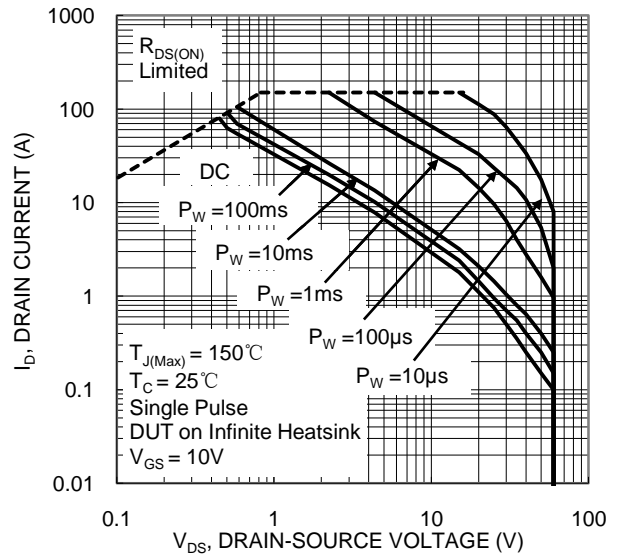


Figure 12 SOA, Safe Operation Area

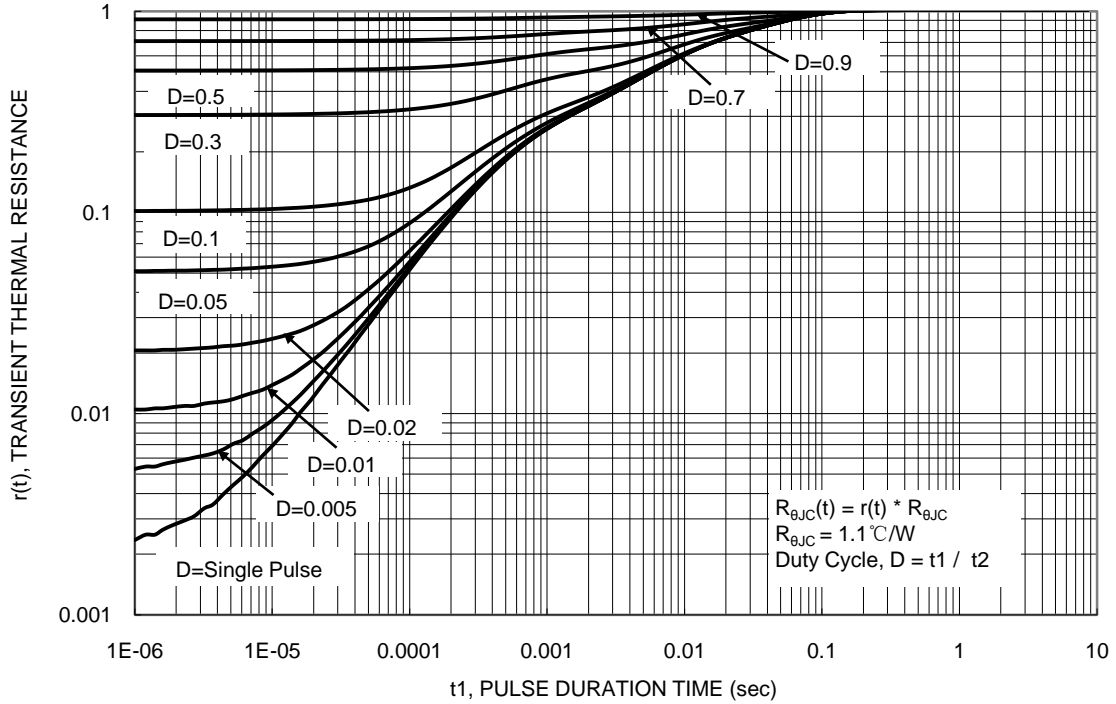
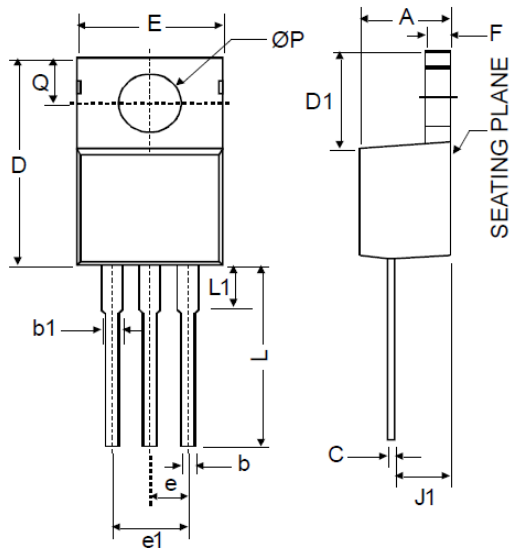


Figure 13 Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO220-3



TO220-3		
Dim	Min	Max
A	3.55	4.85
b	0.51	1.14
b1	1.14	1.78
C	0.31	1.14
D	14.20	16.50
D1	5.84	6.86
E	9.70	10.70
e	2.79	2.99
e1	4.83	5.33
F	0.51	1.40
J1	2.03	2.92
L	12.72	14.72
L1	3.66	6.35
P	3.53	4.09
Q	2.54	3.43
<b>All Dimensions in mm</b>		

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